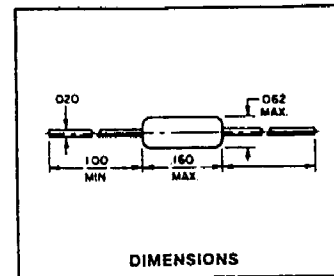


1N5605 1N5606 1N5607 1N5608 1N5609
GENERAL PURPOSE DIODES

GENERAL PURPOSE SILICON DIODES

This device is a Silicon Double Plug Diode for general purpose use in computer, industrial and military applications.



ABSOLUTE MAXIMUM RATINGS

Storage temperature range, T_{stg} -65°C to $+200^{\circ}\text{C}$
Lead or terminal temperature at a distance not less than
 $1/16''$ from the seated surface (or case) for 15 seconds $+275^{\circ}\text{C}$

	1N5605	1N5606	1N5607	1N5608/9
Reverse voltage, 25°C , free air	70 V	150 V	200 V	120 V
Maximum steady state power dissipation at 25°C , free air	250mw	200mw	200mw	250mw
Derating factor				2mw/ $^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

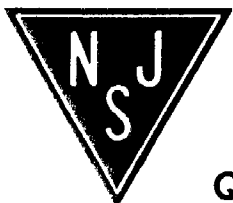
	1N5605		1N5606*		1N5607*	
	MIN	MAX	MIN	MAX	MIN	MAX
Forward Voltage, V_f @ $I_f = 20 \text{ ma}$		1.0 V		1.0 V		1.0 V
Breakdown Voltage, B_{vr} $I_r = 100 \text{ ua}$	70 V		150 V		200 V	
Reverse Current, I_r @ $V_r = 60 \text{ V}$		25 na		25 na		25 na
Reverse Current, I_r @ $V_r = 60 \text{ V}$ @ 150°C		5 ua		5 ua		5 ua

* $I_f = 7 \text{ ma}$, $V_r = 125 \text{ V}$ * $I_f = 3 \text{ ma}$, $V_r = 175 \text{ V}$

1N5605 1N5606 1N5607 1N5608

ELECTRICAL CHARACTERISTICS — 1N5608

	MIN	MAX
Forward Voltage, V_f @ $I_f = 100 \text{ ma}$		1.0 V
Breakdown Voltage, B_{vr} $I_r = 100 \text{ ua}$	120 V	
Reverse Current, I_r @ 50 V		50 na
Reverse Current, I_r @ 50 V @ 150°C		25 ua
*Reverse Recovery Time, T_{rr} $I_f = 5 \text{ ma}$, $V_r = 40 \text{ V}$ $R_1 = 2 \text{ K}$, $C_1 = 10 \text{ pf}$ Recover to 80K ohms		300 nsec



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